

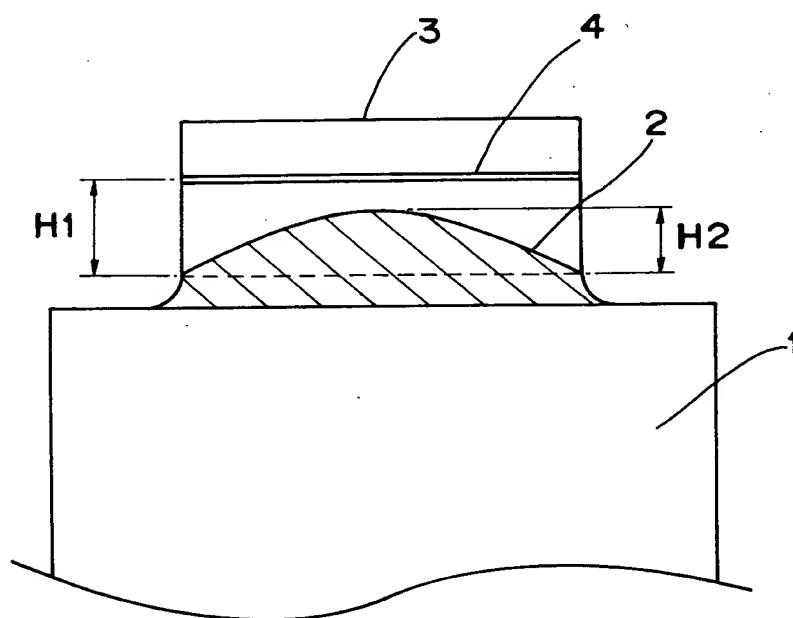
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BY CLASS/CLAS
DATE/DATE

Sheet Title: SEMICONDUCTOR LASER MANUFACTURING  
METHOD AND SEMICONDUCTOR LASER  
First Inventor: Tetsuyoshi INOUE  
Application No.: NEW  
Docket No.: 204552021700

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Washington, D.C. 20006-1888  
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Sheet 1 of 7

Fig. 1



0987010-11301

Fig.2A

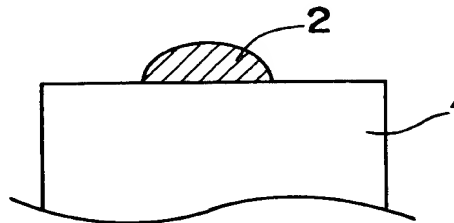


Fig.2B

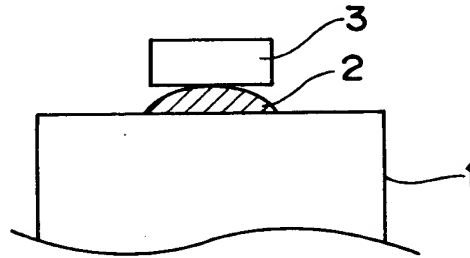


Fig.2C

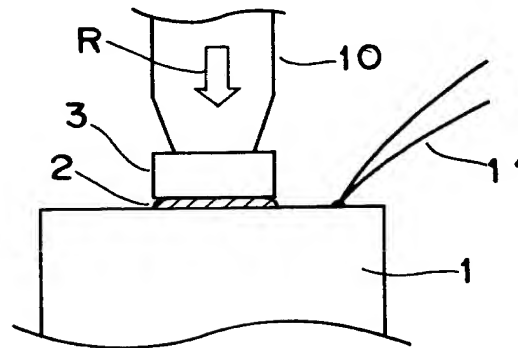
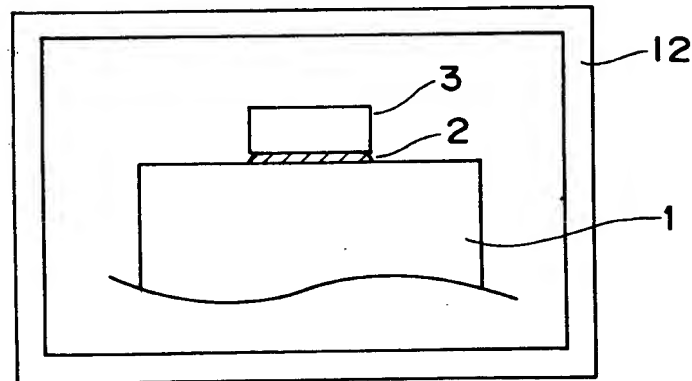


Fig.2D



DATE: 06/03/00	BY: C. G. HIG.
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 METHOD AND SEMICONDUCTOR LASER  
 Filed Inventor: Tetsuyoshi INOUE  
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Fig.3

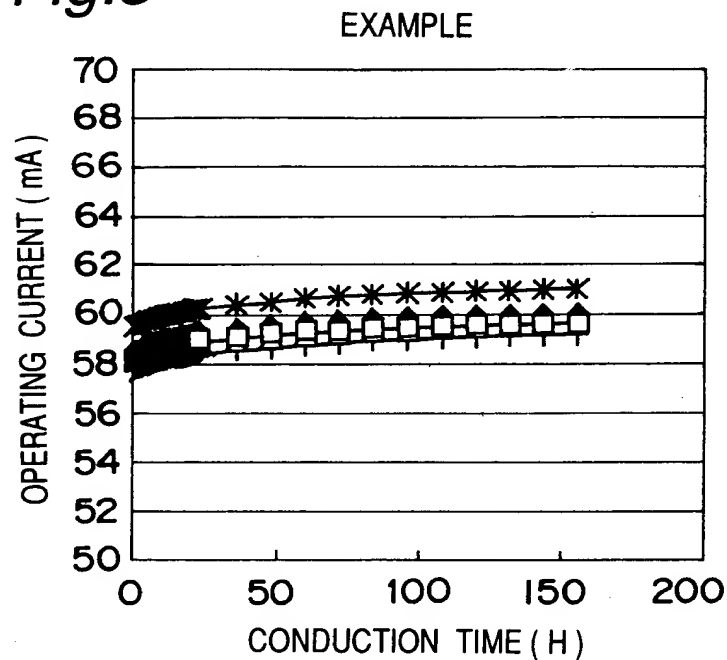
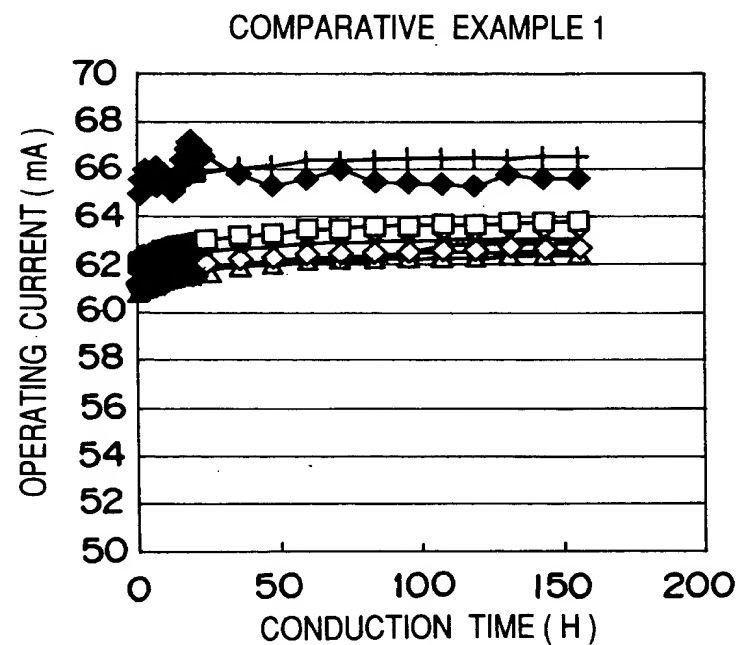


Fig.4



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APPROVED	C.G. FIG.
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Fig.5

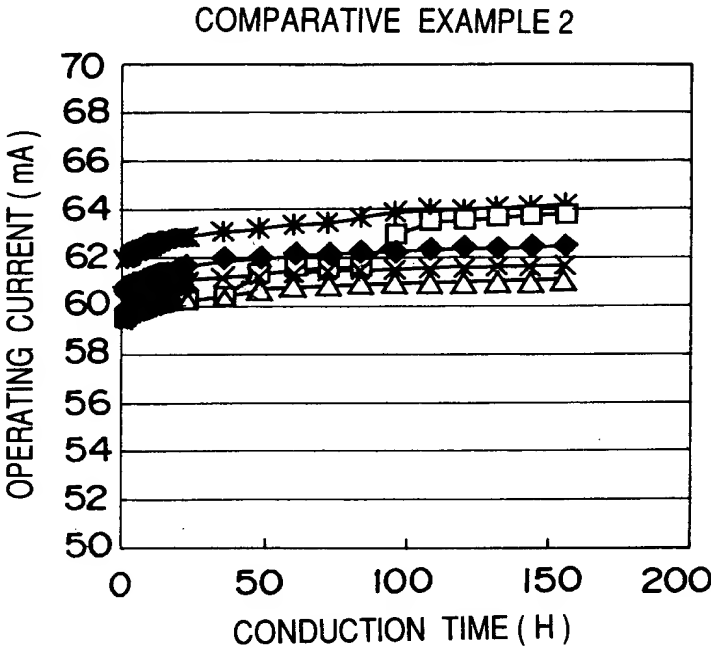
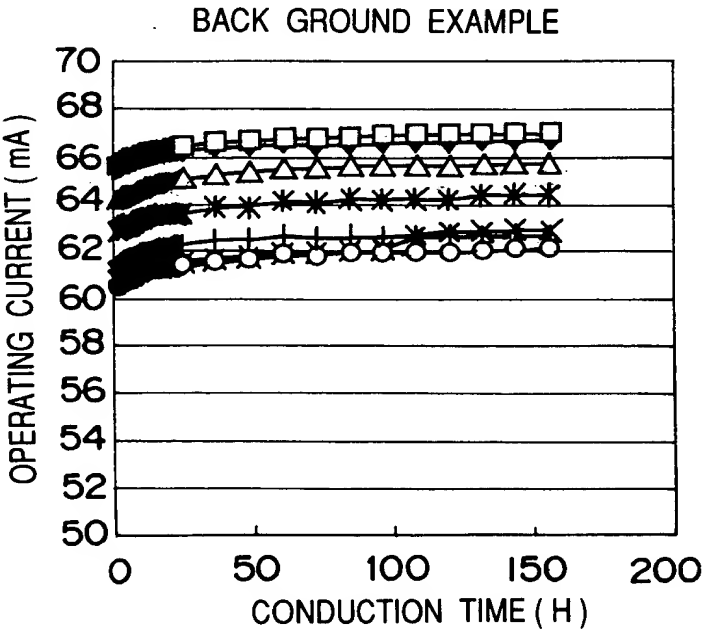


Fig.6



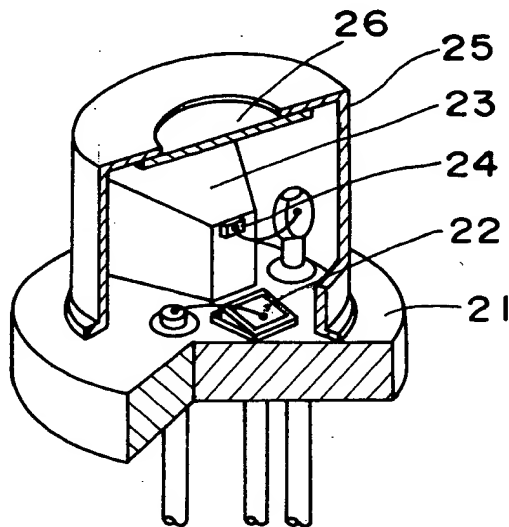
APPROVED	C.G. FIG.
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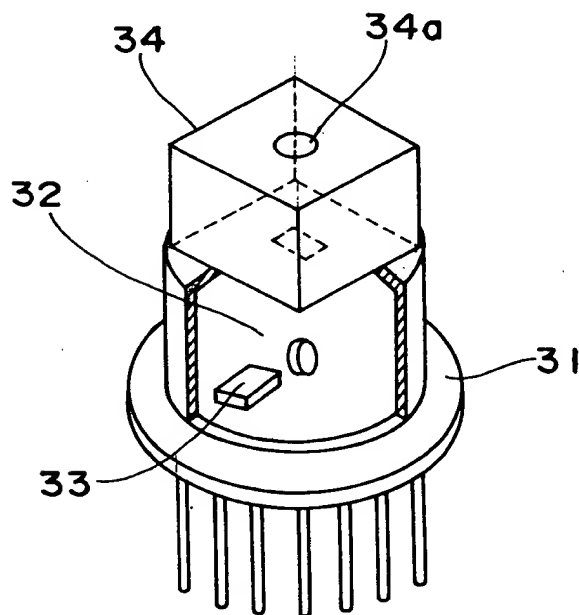
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*Fig.7 BACK GROUND ART*



*Fig.8 BACK GROUND ART*



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APPROVED TO G. FIG.	
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Short Title: SEMICONDUCTOR LASER MANUFACTURING  
 METAL AND SEMICONDUCTOR LASER  
 First Inventor: Tetsuyoshi INOUE  
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Fig.9A

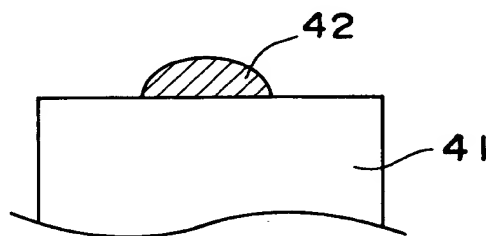


Fig.9B

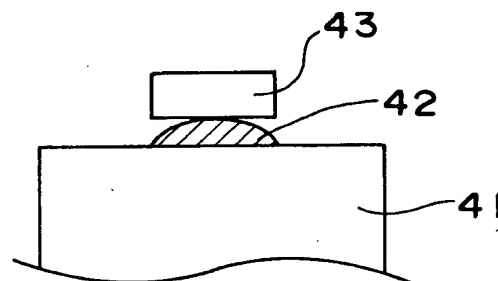
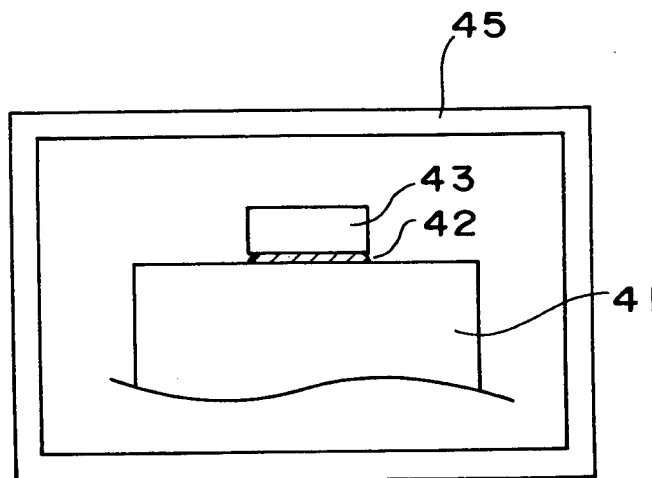


Fig.9C



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Fig. 10A

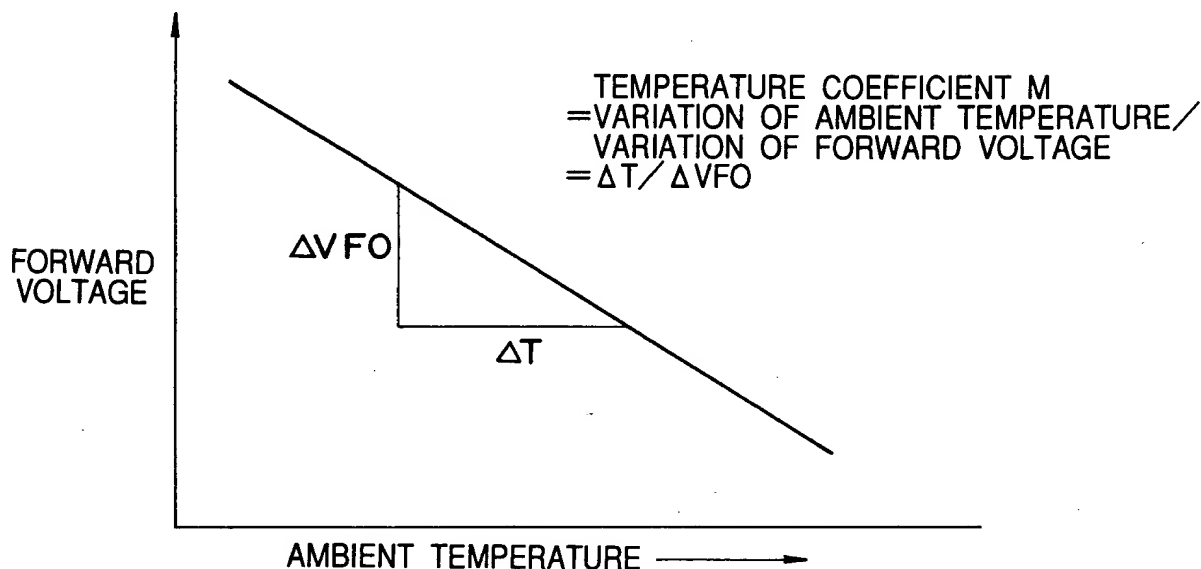


Fig. 10B

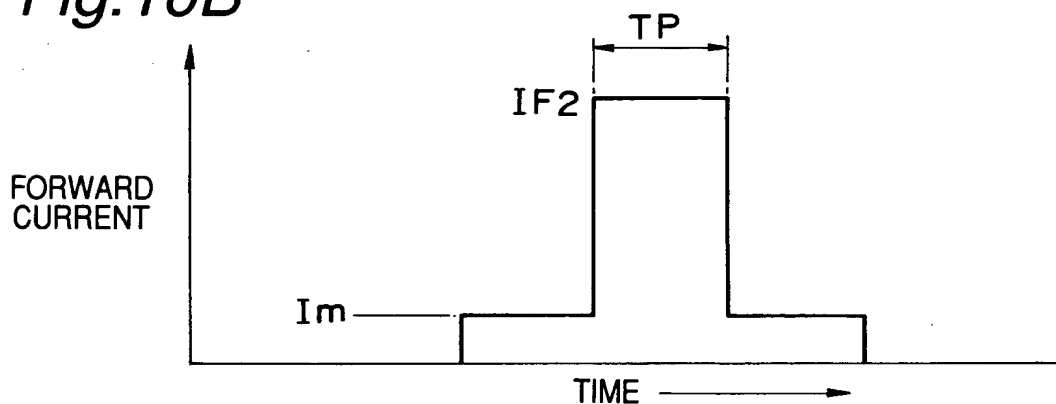
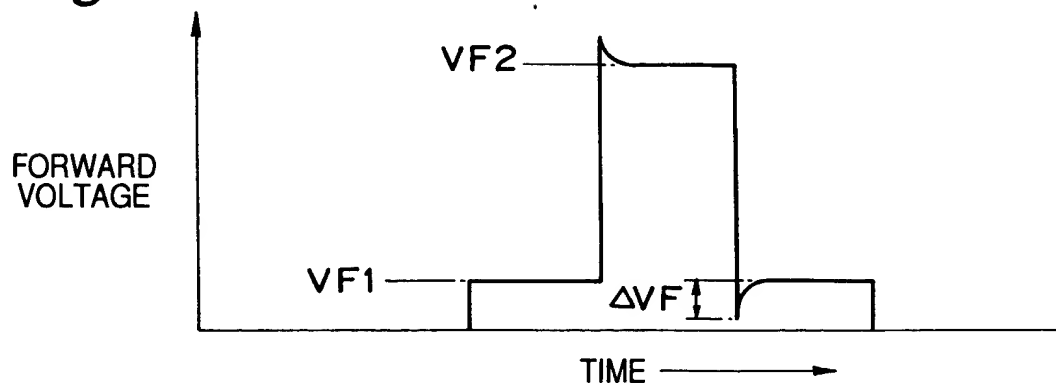


Fig. 10C



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 D007-010/8660